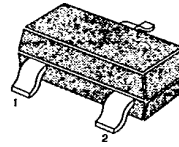


**MMBC1623L5****NPN EPITAXIAL SILICON TRANSISTOR****AMPLIFIER TRANSISTOR****ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	50	V
Collector-Emitter Voltage	$V_{CE0}$	40	V
Emitter-Base Voltage	$V_{EB0}$	5.0	V
Collector Current	$I_C$	100	mA
Collector Dissipation	$P_C$	350	mW
Storage Temperature	$T_{stg}$	150	$^\circ\text{C}$

• Refer to MMBC1623L3 for graphs

SOT-23

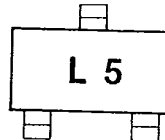


1. Base 2. Emitter 3. Collector

**ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )**

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=40\text{V}, I_E=0$		100	nA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$		100	nA
DC Current Gain	$h_{FE}$	$V_{CE}=6\text{V}, I_C=1.0\text{mA}$	135	270	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		1.0	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C=1.0\text{mA}, V_{CE}=6\text{V}$	0.6	0.7	V
Current Gain-Bandwidth Product	$f_T$	$V_{CE}=6\text{V}, I_E=10\text{mA}$ $f=100\text{MHz}$	200		MHz

Marking



3

